A 1.8-V Operation RFCMOS Transceiver for Bluetooth

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This paper describes a single-chip Bluetooth transceiver LSI, which uses a standard 0.18μm bulk CMOS process. It can operate at a supply voltage of 1.8V, and includes even a low loss transmit/receive antenna switch(SW) in order to realize high level integration. For lower chip area, a channel selection filter consists of simple linearized source-coupled pairs, and the transceiver occupies 10.2mm^2.